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Publisher Correction: Ballistic geometric resistance resonances in a single surface of a topological insulator

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In the original version of this Article, the second and third sentences of the first paragraph of the “Gate voltage and antidot period dependencies” section of the Results originally incorrectly read “The characteristic evolution of the sheet resistance $\rho_\square$=$\rho_\square$ (B=0), with V_g shown for three antidot samples and an unpatterned reference sample in Fig. 3a. The maxima of ρ_{xx}, located between V_g~0.5 and 1 V, reflect the charge neutrality point (CNP), corresponding to an E_F position located slightly in the valence band (see band structure in Fig. 3b).” In the corrected version, “$\rho_\square = \rho_\square(B = 0)$” is replaced by “$\rho_\square = \rho_{xx}(B = 0)$”, and “The maxima of ρ_{xx}” is replaced by “The maxima of $\rho_\square$”.

These errors have been corrected in both the PDF and HTML versions of the Article.

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